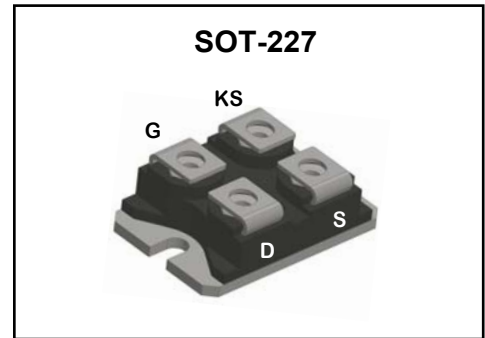
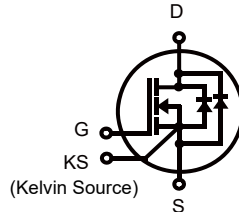


SiC MOSFET Power Module

Features

- ◆ $V_{DSS} = 1200V$
- ◆ $R_{DS(ON)}$ typ. $11m\Omega @ V_{GS} = 18V$
- ◆ SiC-Schottky diode
- ◆ High speed switching with low capacitances
- ◆ Easy to parallel and simple to drive
- ◆ Real Kelvin Source Connection
- ◆ Pb Free & RoHS Compliant
- ◆ Electrically Isolation base plate

Preliminary



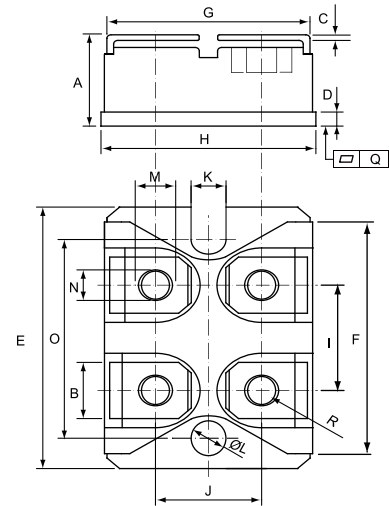
Dimensions in inches and (millimeters)

Applications

- ◆ Solar Inverters
- ◆ UPS
- ◆ Motor Drive
- ◆ Induction heating
- ◆ Switch Mode Power Supplies
- ◆ Battery Chargers
- ◆ DC/DC Converters

Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Ratings	Unit	
Drain-Source Voltage	V_{DS}	1200	V	
Gate-Source Voltage (dynamic)	$V_{GS(max)}$	-10/+23	V	
Gate-Source Voltage (static)	$V_{GS(OP)}$	-4/+18	V	
Drain Current-Continuous	I_D	@ $T_c = 25^\circ C$ @ $T_c = 100^\circ C$	172 120	A
Drain Current-Pulsed	I_{DM}	@ $T_c = 25^\circ C$	344	A
Maximum Power Dissipation	P_D	714	W	
Storage Temperature Range	T_{STG}	-40 to +125	$^\circ C$	
Operating Junction Temperature Range	T_{VJ}	-40 to +175	$^\circ C$	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.21	$^\circ C/W$	
Isolation Voltage (A.C. 1 minute) between All Terminals and Baseplate	V_{iso}	2500	V	
Mounting torque (M4 Screw)	To heatsink To terminals	M_d	1.3 1.1	N_m

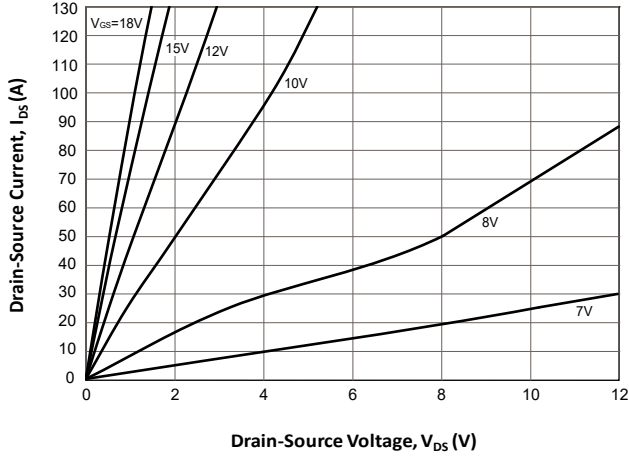
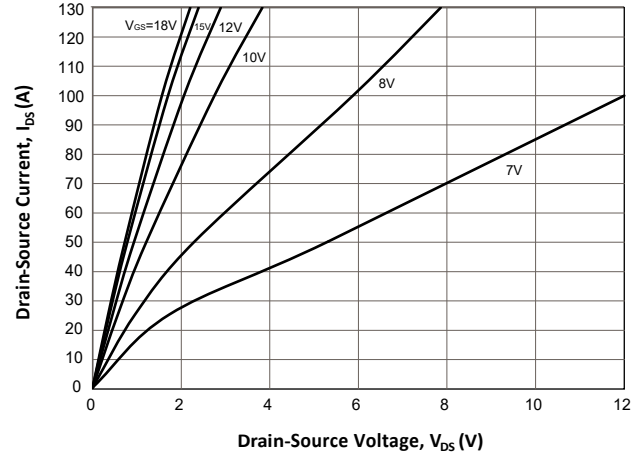
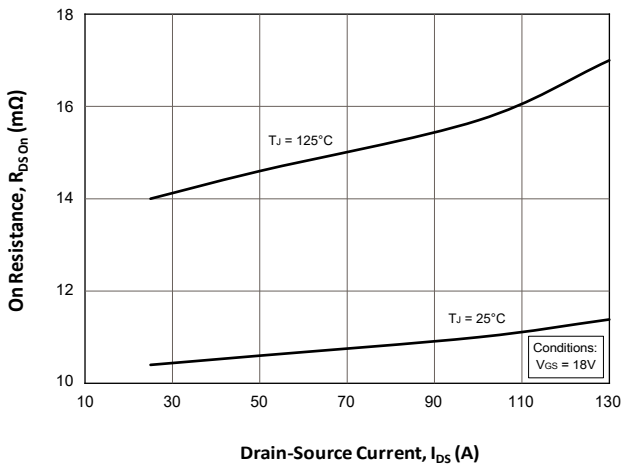
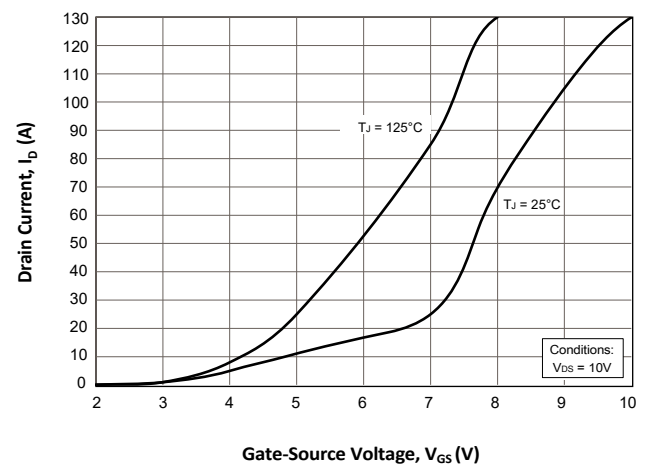
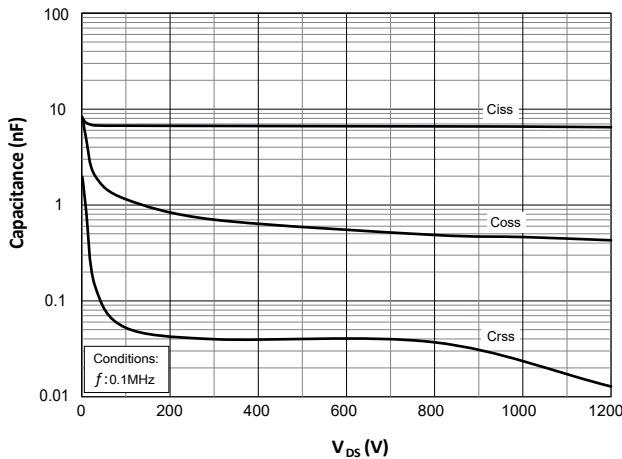
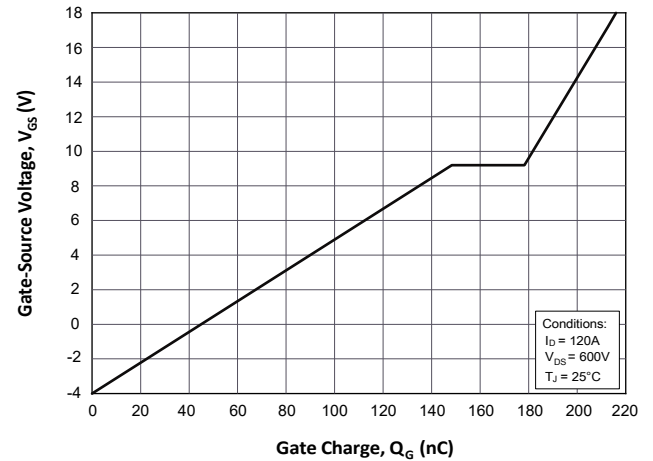


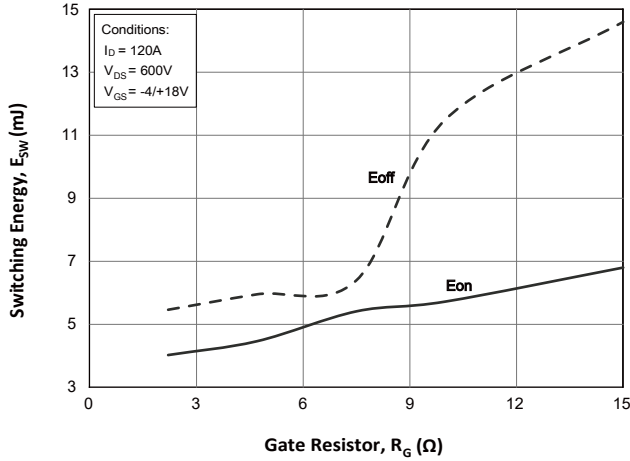
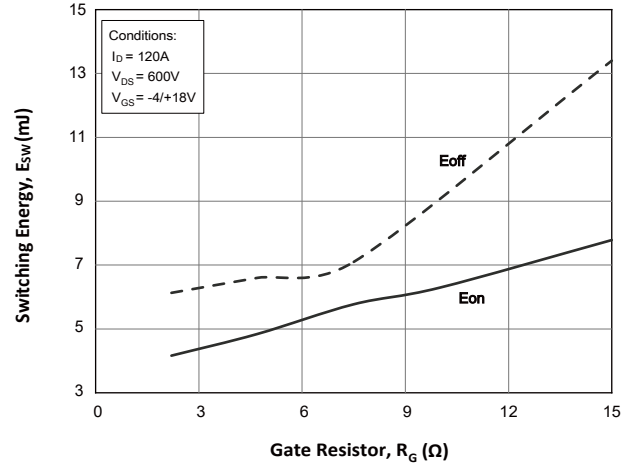
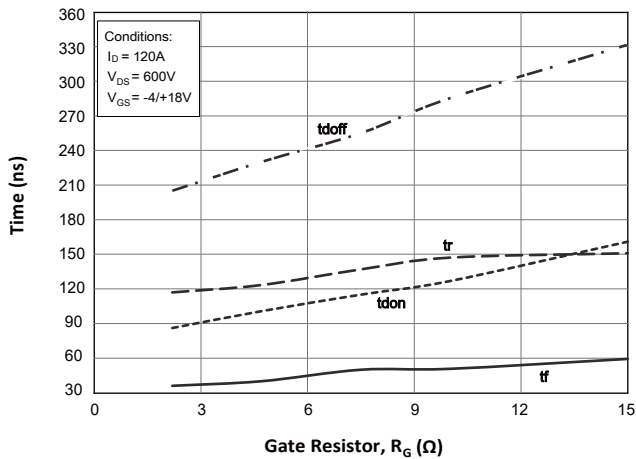
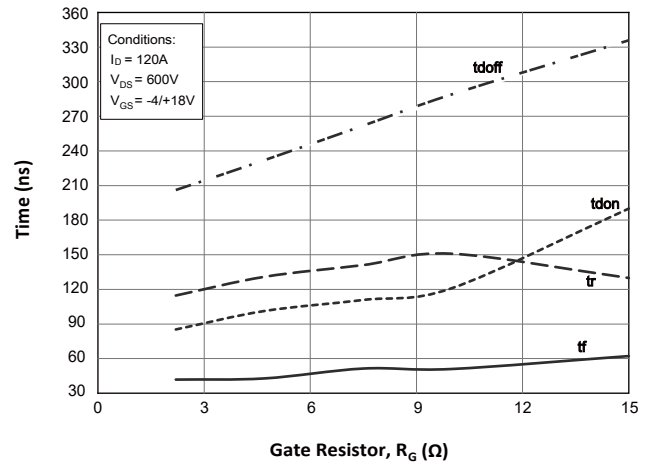
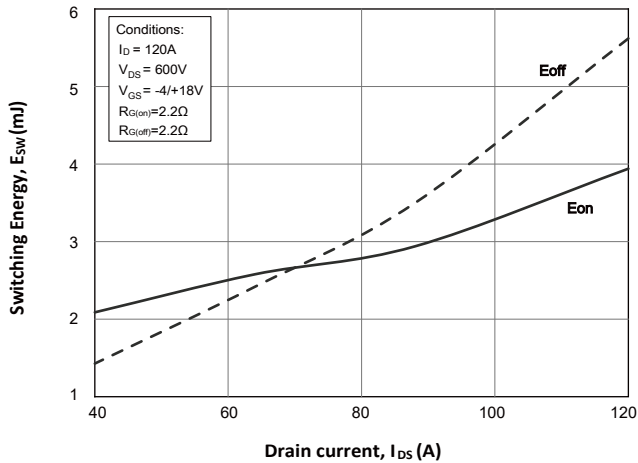
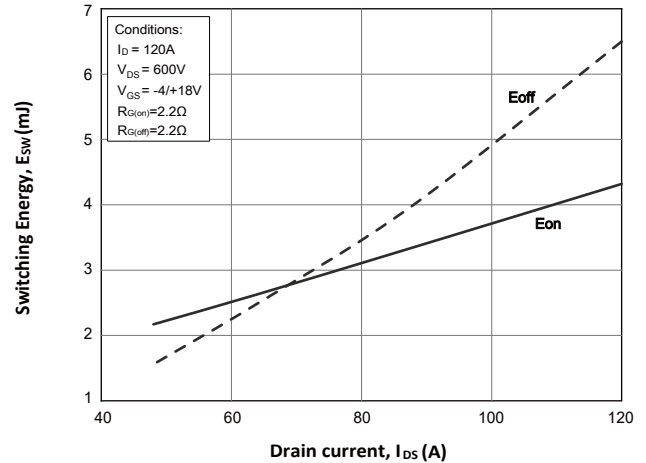
	DIMENSIONS			
	INCHES		MM	
	MIN	MAX	MIN	MAX
A	0.460	0.483	11.68	12.28
B	0.307	0.323	7.80	8.20
C	0.030	0.033	0.75	0.85
D	0.071	0.081	1.80	2.05
E	1.488	1.504	37.80	38.20
F	1.248	1.260	31.70	32.00
G	0.917	0.957	23.30	24.30
H	0.996	1.008	25.30	25.60
I	0.579	0.602	14.70	15.30
J	0.492	0.516	12.50	13.10
K	0.161	0.169	4.10	4.30
L	0.161	0.169	4.10	4.30
M	0.181	0.197	4.60	5.00
N	0.165	0.181	4.20	4.60
O	1.181	1.197	30.00	30.40
Q	-0.002	0.004	-0.05	0.10
R	M4*8			

Electrical Characteristics @ $T_{VJ} = 25^{\circ}\text{C}$ (unless otherwise specified)

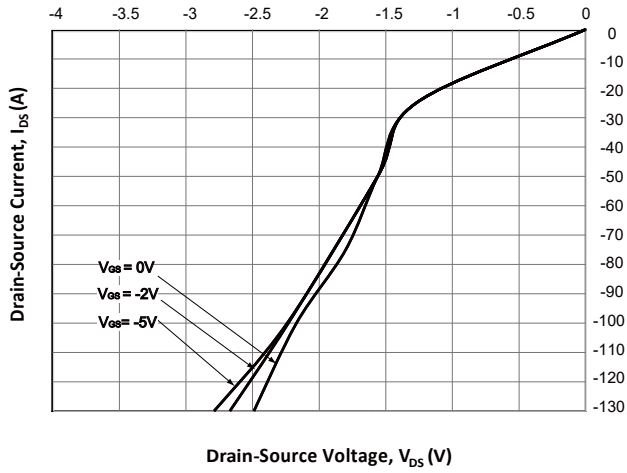
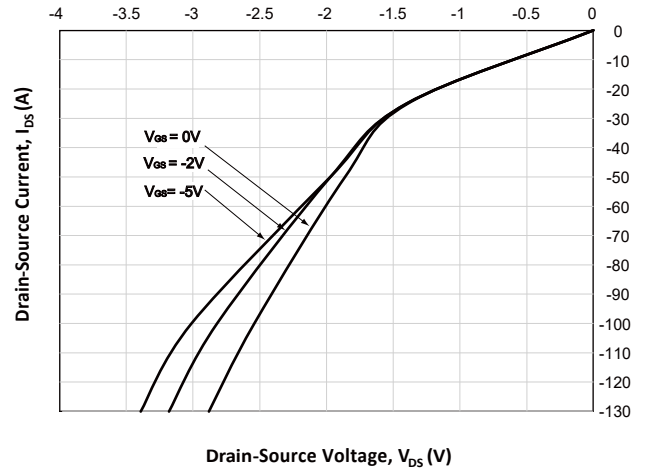
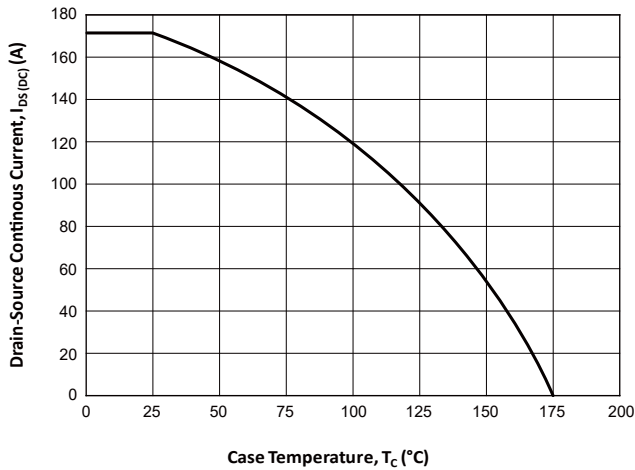
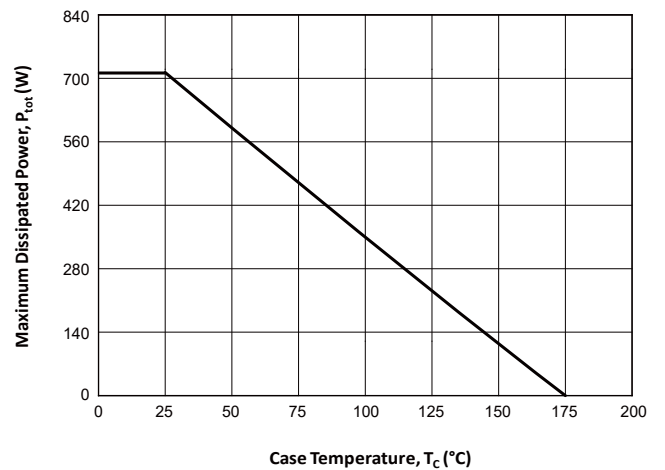
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
OFF Characteristics							
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_{DS} = 0.2mA$	1200	-	-	V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0V, V_{DS} = 1200V$	-	-	200	μA	
Gate-Body Leakage	I_{GSS}	$V_{GS} = 20V, V_{DS} = 0V$	-	-	500	nA	
ON Characteristics							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{DS} = 8mA$	2.0	2.9	4.1	V	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 18V, I_{DS} = 100A$	-	11	14.3	m Ω	
Gate Resistance	$R_{G(int)}$	Internal gate resistor	$T_{VJ} = 25^{\circ}\text{C}$	-	11.24	Ω	
Dynamic Characteristics							
Input Capacitance	C_{iss}	$V_{DS} = 800V$ $V_{GS} = 0V$ $V_{AC} = 1V$ Freq. = 100KHz	-	6.61	-	nF	
Output Capacitance	C_{oss}		-	0.49	-		
Reverse Transfer Capacitance	C_{rss}		-	0.04	-		
Total Gate Charge	Q_g	$V_{DS} = 600V$ $V_{GS} = -4V/+18V$ $I_{DS} = 120A$	-	216	-	nC	
Gate to Source Charge	Q_{gs}		-	148	-		
Gate to Drain Charge	Q_{gd}		-	30	-		
Switching Characteristics							
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 600V$ $V_{GS} = -4/+18V$ $I_{DS} = 120A$ $R_{G(on)} = 2.2\Omega$ $R_{G(off)} = 2.2\Omega$	$T_{VJ} = 25^{\circ}\text{C}$	-	95	-	ns
			$T_{VJ} = 150^{\circ}\text{C}$	-	85	-	
Rise Time	t_r		$T_{VJ} = 25^{\circ}\text{C}$	-	125	-	
			$T_{VJ} = 150^{\circ}\text{C}$	-	115	-	
Turn-Off Delay Time	$t_{d(off)}$		$T_{VJ} = 25^{\circ}\text{C}$	-	181	-	
			$T_{VJ} = 150^{\circ}\text{C}$	-	206	-	
Fall Time	t_f		$T_{VJ} = 25^{\circ}\text{C}$	-	31	-	
			$T_{VJ} = 150^{\circ}\text{C}$	-	42	-	
Turn-On Switching Energy	E_{on}		$T_{VJ} = 25^{\circ}\text{C}$	-	3.9	-	mJ
			$T_{VJ} = 150^{\circ}\text{C}$	-	4.2	-	
Turn-Off Switching Energy	E_{off}	$T_{VJ} = 25^{\circ}\text{C}$	-	5	-		
		$T_{VJ} = 150^{\circ}\text{C}$	-	6.1	-		
SiC Schottky Diode Characteristics at $T_J = 25^{\circ}\text{C}$, unless otherwise specified							
Continuous Diode Fwd Current	I_{SDC}	$V_{GS} = 0V$	-	120	-	A	
Drain-Source Reverse Voltage	V_{SD}	$I_{SD} = 75A, V_{GS} = 0V$	-	1.8	-	V	
MOSFET Forward Recovery Charge	Q_{rr}	$V_{DD} = 600V$ $I_{DS} = 120A$ $V_{GS} = -4/+18V$ $di/dt = 1900 A/\mu s$	$T_{VJ} = 25^{\circ}\text{C}$	-	1028	-	nC
			$T_{VJ} = 150^{\circ}\text{C}$	-	3009	-	
MOSFET Peak Forward Recovery Current	I_{rrm}		$T_{VJ} = 25^{\circ}\text{C}$	-	24	-	A
			$T_{VJ} = 150^{\circ}\text{C}$	-	36	-	
MOSFET Reverse Recovery Time	T_{rr}		$T_{VJ} = 25^{\circ}\text{C}$	-	89	-	ns
			$T_{VJ} = 150^{\circ}\text{C}$	-	130	-	

Notes:
1. Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $> 2\%$.

Typical Characteristics
Fig.1 Output Characteristics at $T_J = 25^\circ\text{C}$

Fig.2 Output Characteristics at $T_J = 125^\circ\text{C}$

Fig.3 Drain Source on Resistance

Fig.4 Transfer Characteristics

Fig.5 Capacitances vs. Drain-Source Voltage

Fig.6 Gate Charge Characteristics


Typical Characteristics
Fig.7 Switching losses vs R_G change $T_J=125^\circ\text{C}$

Fig.8 Switching losses vs R_G change $T_J=150^\circ\text{C}$

Fig.9 Switching Timer vs R_G Change $T_J=125^\circ\text{C}$

Fig.10 Switching Timer vs R_G Change $T_J=150^\circ\text{C}$

Fig.11 Clamped Inductive Switching Energy vs. Drain Current $T_J=125^\circ\text{C}$

Fig.12 Clamped Inductive Switching Energy vs. Drain Current $T_J=150^\circ\text{C}$


Typical Characteristics

Fig.13 SiC Schottky Diode curves $T_J = 25^\circ\text{C}$

Fig.14 SiC Schottky Diode curves $T_J = 125^\circ\text{C}$

Fig.15 Continuous Drain Current (MOSFET) vs. Case Temperature

Fig.16 Max. Power Dissipation (MOSFET) Derating vs. Case Temperature


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